





#### NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

### **Features**

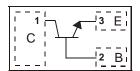
- **Epitaxial Die Construction**
- Ultra-Small Leadless Surface Mount Package
- Ultra Low Profile (0.4mm max)
- Complementary PNP Type Available (BC857BLP4)
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: DFN1006H4-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections Indicator: Collector Dot
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Ordering Information: See Page 3
- Marking Information: See Page 3
- Weight: 0.0008 grams (approximate)







Top View Internal Schematic

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	100	mA

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @T <sub>A</sub> = 25°C	$P_{D}$	250	mW
Thermal Resistance, Junction to Ambient (Note 3) @T <sub>A</sub> = 25°C	$R_{ hetaJA}$	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

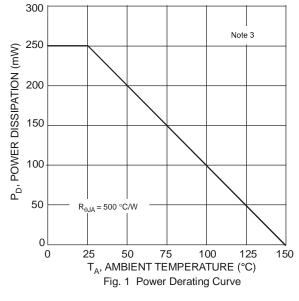
Characteristic (Note 4)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	50	1		<b>V</b>	$I_C = 10\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	45	1		<b>V</b>	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6	1		<b>V</b>	$I_E = 1\mu A, I_C = 0$
DC Current Gain	h <sub>FE</sub>	200	350	450	I	$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		80 200	250 600	mV	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 100$ mA, $I_B = 5.0$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		700 900	_	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Voltage	V <sub>BE(ON)</sub>	580 —	640 725	700 770	mV	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA
Collector-Cutoff Current	I <sub>CBO</sub>			15 5.0	nΑ μΑ	V <sub>CB</sub> = 30V V <sub>CB</sub> = 30V, T <sub>A</sub> = 150°C
Gain Bandwidth Product	f <sub>T</sub>	100			MHz	$V_{CE} = 5.0V$ , $I_{C} = 10mA$ , $f = 100MHz$
Collector-Base Capacitance	$C_{CBO}$	_	3.0	_	рF	$V_{CB} = 10V, f = 1.0MHz$

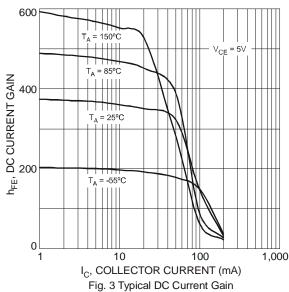
Notes:

- 1. No purposefully added lead.
- Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php
  Device Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php
  Diodes Inc. suggested pad layout document AP02001 on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Short duration pulse test used to minimize self-heating effect.

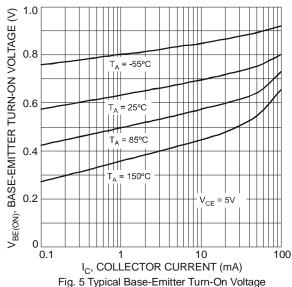








vs. Collector Current



vs. Collector Current

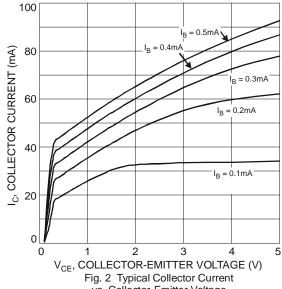


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

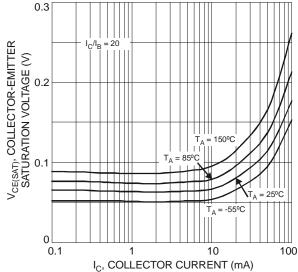


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

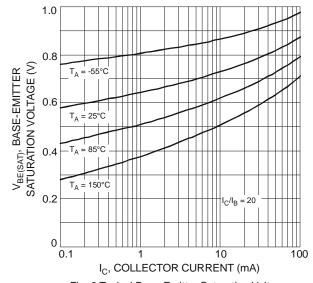


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

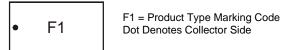


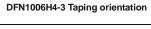
# Ordering Information (Note 5)

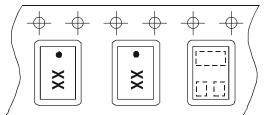
Part Number	Case	Packaging
BC847BLP4-7	DFN1006H4-3	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**

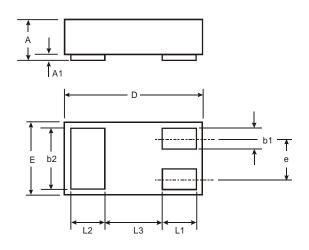






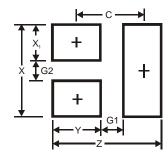
Direction of feed

# **Package Outline Dimensions**



DFN1006H4-3				
Dim	Min	Max	Тур	
Α	_	0.40	_	
A1	0	0.05	0.02	
b1	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
е	_		0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3			0.40	
All Dimensions in mm				

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
С	0.7



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